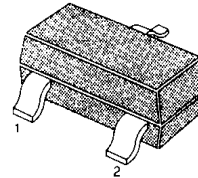


KST5086/5087**PNP EPITAXIAL SILICON TRANSISTOR****LOW NOISE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS (T_A=25 °C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-3	V
Collector Current	I _C	-50	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{STG}	150	°C

SOT-23



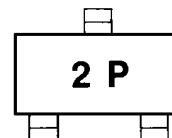
1. Base 2. Emitter 3. Collector

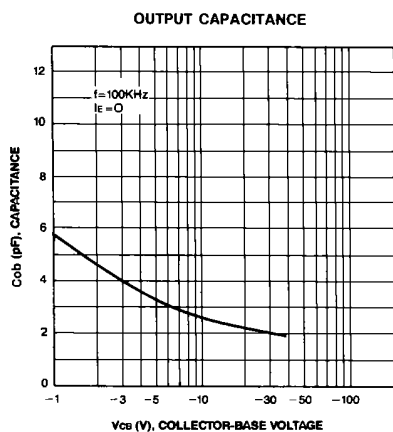
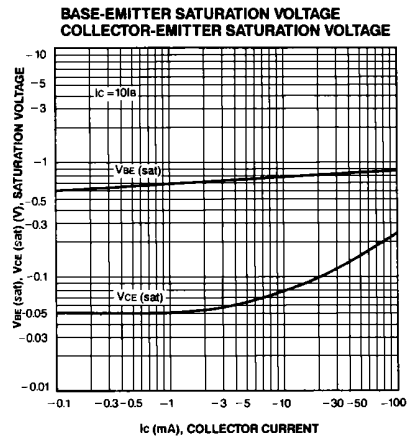
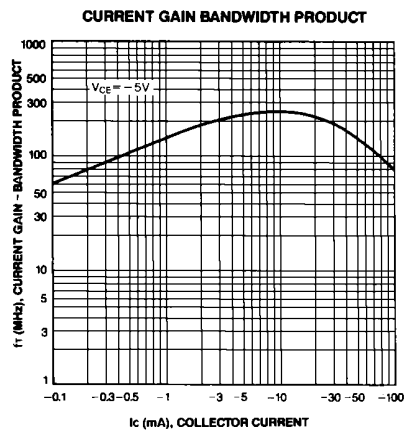
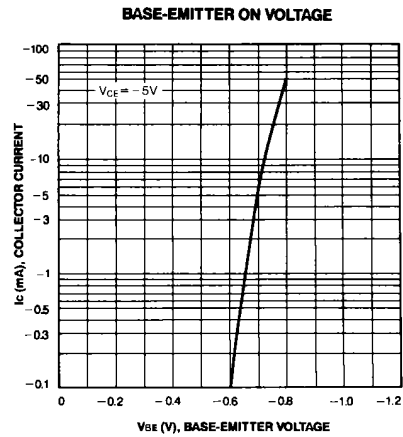
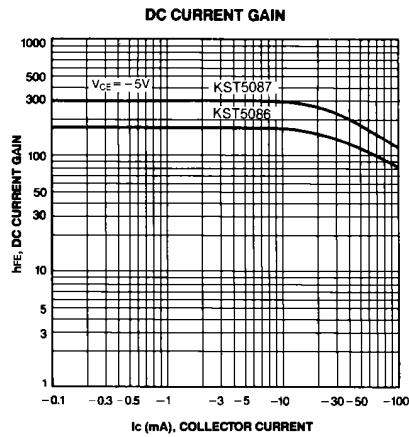
ELECTRICAL CHARACTERISTICS (T_A=25 °C)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = -100 μA, I _E =0	-50		V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = -1mA, I _B =0	-50		V
Collector Cut-off Current	I _{CBO}	V _{CB} = -20V, I _E =0		-50	nA
DC Current Gain	h _{FE}	V _{CE} = -5V, I _C = -100 μA	150	500	
:KST5086			250	800	
:KST5087		V _{CE} = -5V, I _C = -1mA	150		
:KST5086			250		
:KST5087		V _{CE} = -5V, I _C = -10mA	150		
:KST5086			250		
:KST5087					
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA		-0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = -10mA, I _B = -1mA		-0.85	V
Current Gain-Bandwidth Product	f _T	V _{CE} = -5V, I _C = -500 μA f=20MHz	40		MHz
Collector-Base Capacitance	C _{OB}	V _{CB} = -5V, I _E =0 f=100MHz		4	pF
Noise Figure	NF	I _C = -100 μA, V _{CE} = -5V R _S =3kΩ, f=1KHz			
KST5086				3	dB
KST5087		V _{CE} = -5V, I _C = -20mA		2	dB
KST5087		R _S =10kΩ f=10Hz to 15.7KHz		2	dB

MARKING CODE

TYPE	KST5086	KST5087
MARK	2P	2Q

Marking



KST5086/5087

PNP EPITAXIAL SILICON TRANSISTOR
